



P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	RDS(ON) Max	I _D Tc = +25°C
-40V	15mΩ @ V _{GS} = -10V	-61A
-40 V	23mΩ @ V _{GS} = -4.5V	-49A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Reverse polarity protections
- **BLDC** motor controls
- Power-management functions

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP4013SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

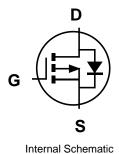
https://www.diodes.com/quality/product-definitions/

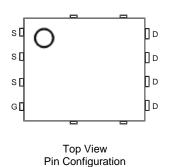
Mechanical Data

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

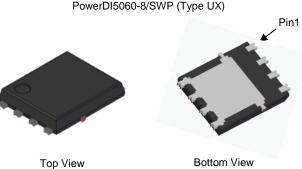
Site 1:

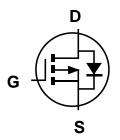






Site 2:





D s[Īο D s[Īο GГ Top View

Pin Configuration

- **Bottom View**
- Internal Schematic

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



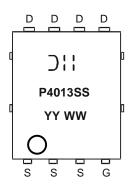
Ordering Information (Note 4)

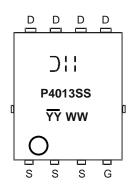
Part Number Package	Packago	Packing		
	Fackage	Qty.	Carrier	
DMP4013SPSQ-13	PowerDI5060-8	2,500	Reel	
DMP4013SPSQ-13	PowerDI5060-8/SWP (Type UX)	2,500	Reel	

Note:

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





⊃ I I = Manufacturer's Marking
P4013SS = Product Type Marking Code
YYWW or YYWW = Date Code Marking
YY or YY= Year (ex: 23 = 2023)
WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	-40	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current V _{GS} = -10V (Note 7)	Steady State	T _C = +25°C T _C = +70°C	lο	-61 -49	А
Continuous Drain Current V _{GS} = -10V (Note 6)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lο	-11 -9	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-244	Α
Maximum Body Diode Continuous Current (Note 7)			Is	-61	Α
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			lsм	-244	Α
Avalanche Current (Note 8) L = 1mH			I _{AS}	-16	Α
Avalanche Energy (Note 8) L = 1mH			Eas	176	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	96	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	44	°C/W
Thermal Resistance, Junction to Case (Note 7)		Reлc	1.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

$\textbf{Electrical Characteristics} \ (@T_A = +25^{\circ}C, \ unless \ \ \underline{otherwise \ specified.})$

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	-40	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	$V_{DS} = -40V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(TH)	-1	_	-3	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance	Process		9.6	15	mΩ	$V_{GS} = -10V, I_{D} = -10A$	
Static Dialii-Source On-Resistance	RDS(ON)		13.4	23	1117.5	$V_{GS} = -4.5V, I_{D} = -8A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	4004	_		V _{DS} = -20V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss		309	_	pF		
Reverse Transfer Capacitance	Crss	_	229	_			
Gate Resistance	R_g		3.5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (VGS = -4.5V)	Qg		31	_			
Total Gate Charge (VGS = -10V)	Qg	_	67	_	nC	$V_{DS} = -20V, I_{D} = -10A$	
Gate-Source Charge	Qgs		13.2	_	IIC		
Gate-Drain Charge	Qgd	_	11	_			
Turn-On Delay Time	tD(ON)	_	9.9	_		V _{GS} = -10V, V _{DD} = -20V, R _G = 3Ω, I _D = -10A	
Turn-On Rise Time	t _R	_	32	_			
Turn-Off Delay Time	t _{D(OFF)}	_	46	_	ns		
Turn-Off Fall Time	t _F	_	53	_			
Reverse Recovery Time	trr	_	19.5	_	ns	IF = -10A, di/dt = -100A/µs	
Reverse Recovery Charge	Q _{RR}	_	11.6	_	nC	I _F = -10A, di/dt = -100A/µs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.



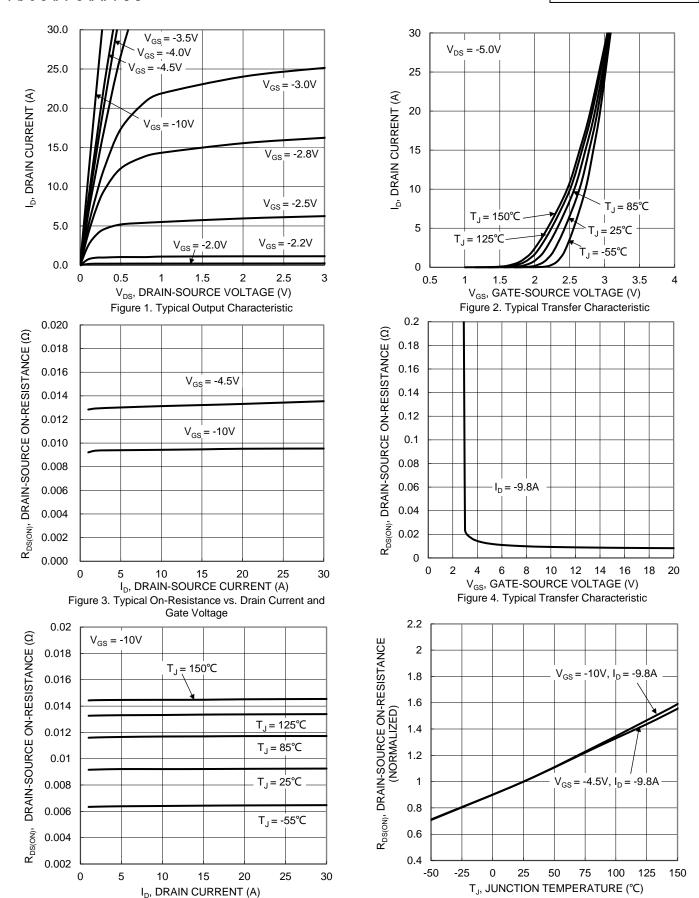
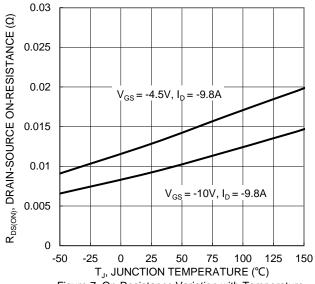
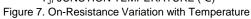


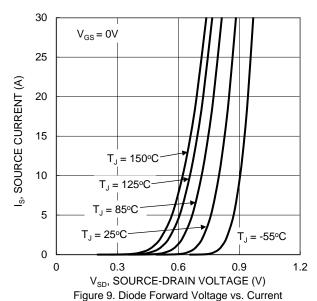
Figure 5. Typical On-Resistance vs. Drain Current and Temperature

Figure 6. On-Resistance Variation with Temperature









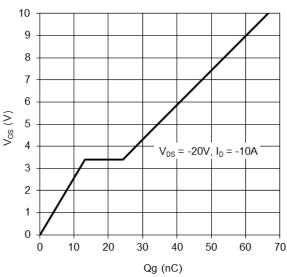


Figure 11. Gate Charge

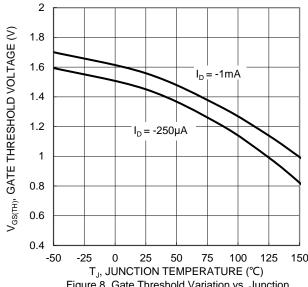


Figure 8. Gate Threshold Variation vs. Junction Temperature

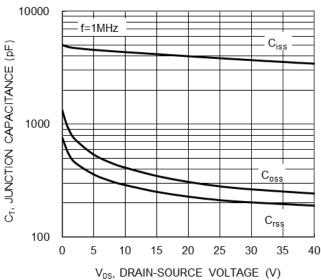


Figure 10. Typical Junction Capacitance

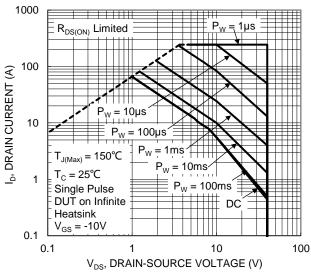


Figure 12. SOA, Safe Operation Area



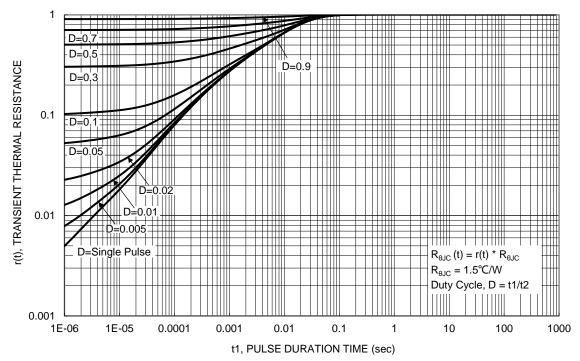


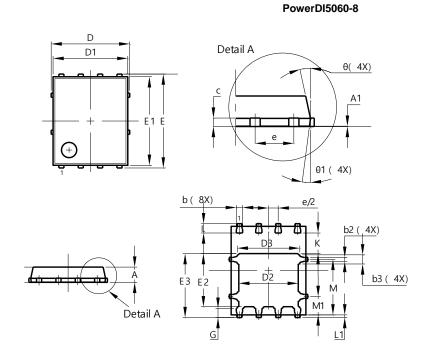
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

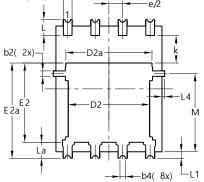
Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

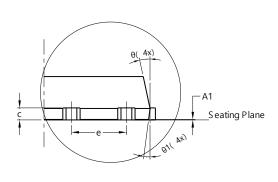


1				
PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A 1	0.00	0.05	_	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D	;	5.15 BSC	;	
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
E	(6.15 BSC	;	
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е	1.27 BSC			
G	0.51	0.71	0.61	
K	0.51	-	_	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
М	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

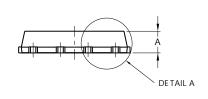
Site 2:



PowerDI5060-8/SWP (Type UX)



DETAIL A



PowerDI5060-8/SWP					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4).25REF			
С	0.230	0.330	0.277		
D	5	.15 BS0)		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78	4.18	3.98		
Е	6	.40 BS0			
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1.27BSC				
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
M	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

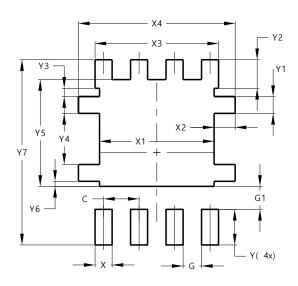


Suggested Pad Layout

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Site 1:

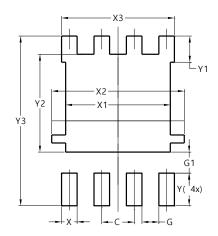
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	5.190
Х3	4.420
Υ	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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